

SANYO	No.1287C	2SA1345/2SC3399
		PNP/NPN Epitaxial Planar Silicon Transistors Switching Applications (with Bias Resistance)

Applications

Switching circuit, inverter, interface circuit, driver

Features

- Built-in bias resistor ($R_1=47k\Omega$, $R_2=47k\Omega$).
- Small-sized package (SPA).

(): 2SA1345

Absolute Maximum Ratings/ $T_a=25^\circ\text{C}$

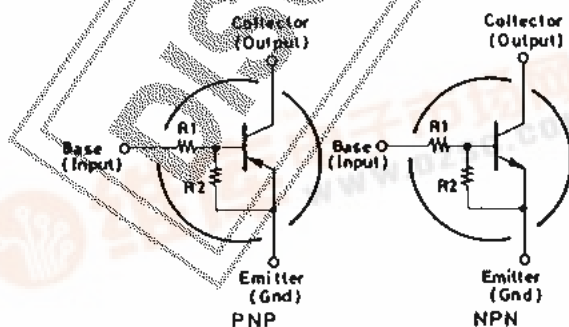
		unit
Collector to Base Voltage	V_{CBO}	(-150) V
Collector to Emitter Voltage	V_{CEO}	(-150) V
Emitter to Base Voltage	V_{EBO}	(-10) V
Collector Current	I_C	(-100) mA
Collector Current(Pulse)	I_{CP}	(-200) mA
Collector Dissipation	P_C	300 mW
Junction Temperature	T_j	150 $^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150 $^\circ\text{C}$

Electrical Characteristics/ $T_a=25^\circ\text{C}$

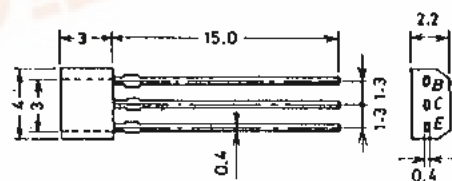
		min	typ	max	unit
Collector Cutoff Current	I_{CBO} $V_{CB}=(-)40V, I_E=0$			(-0.1)	μA
Collector Cutoff Current	I_{CEO} $V_{CE}=(-)40V, I_B=0$			(-0.5)	μA
Emitter Cutoff Current	I_{EBO} $V_{EB}=(-)5V, I_C=0$	(-30)	(-53)	(-80)	μA
DC Current Gain	h_{FE} $V_{CE}=(-)5V, I_C=(-)5mA$	50			
Gain-bandwidth product	f_T $V_{CE}=(-)10V, I_C=(-)5mA$		250 (200)		MHz
Output Capacitance	c_{ob} $V_{CB}=(-)10V, f=1MHz$		3.7 (5.5)		pF
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$ $I_C=(-)5mA, I_B=(-)0.25mA$		(-0.1)	(-0.3)	V

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Electrical Connection



Case Outline 2033
(unit: mm)



B: Base
C: Collector
E: Emitter
SANYO: SPA



Specifications and information herein are subject to change without notice.

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			min	typ	max	unit
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0$	(-)50			V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)100\mu A, R_{BE}=\infty$	(-)50			V
Input Off Voltage	$V_{I(off)}$	$V_{CE}=(-)15V, I_C=(-)100\mu A$	(-)0.8	(-)1.1	(-)1.5	V
Input On Voltage	$V_{I(on)}$	$V_{CE}=(-)0.2V, I_C=(-)15mA$	(-)1.0	(-)2.5	(-)5.0	V
Input Resistance	R_1		32	47	62	k Ω
Input Resistance Ratio	R_1/R_2		0.9	1.0	1.1	

■ Sample Application Circuit

